

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known	
		Application Number	10/696,346
		Filing Date	10-29-03
		First Named Inventor	Srikanth B. Samavedam
		Group Art Unit	2829B
		Examiner Name	C. Chaudhari
Sheet 1 of 1	Attorney Docket Number	SC13102TP	

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
CC	AA	US -6,340,827 B1	01-22-2002	CHOI	
CC	AB	US -6,211,072 B1	04-03-2001	BRENNAN	
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁵

NON PATENT LITERATURE DOCUMENTS		
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published... ⁷
CC	AC	LEMONDS et al., "Adhesion of Cu and Low-K Dielectric Thin Films With Tungsten Carbide," J. Mater. Res., Vol. 17, No. 6, June 2002, Materials Research Society, pp. 1320-1328.
CC	AD	DENG et al., "Reactive Sputtered Titanium Carbide/Nitride and Diamondlike Carbon Coatings," J. Vac. Sci. Technol. A 16(4), Jul/Aug 1998, American Vacuum Society, pp. 2073-2077.
CC	AE	PAN et al., "A Low-Temperature Metal-Doping Technique for Engineering the Gate Electrode of Replacement Metal Gate CMOS Transistors," IEEE Electron Device Letters, Vol. 24, No. 9, September 2003, pp. 347-349.

Examiner Signature	Chandra Chaudhari	Date Considered	1-05
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¹ Unique citation designation number. ² See Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached.

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